

Vishay Semiconductors

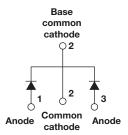
HALOGEN

FREE

HEXFRED®, Ultrafast Soft Recovery Diode, 2 x 15 A



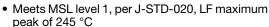
D²PAK (TO-263AB)



PRIMARY CHARACTERISTICS						
I _{F(AV)}	2 x 15 A					
V_{R}	600 V					
V _F at I _F	1.2 V					
t _{rr} (typ.)	19 ns					
T _J max.	150 °C					
Package	D ² PAK (TO-263AB)					
Circuit configuration	Common cathode					

FEATURES

- · Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- · Specified at operating conditions





BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA30TA60CS is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A per leg continuous current, the VS-HFA30TA60CS is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA30TA60CS is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V_{R}		600	V		
Maximum continuous forward current per leg		T _C = 100 °C	15			
per device	P I _F		30	۸		
Single pulse forward current	I _{FSM}		150	Α		
Maximum repetitive forward current	I _{FRM}		60			
Maximum power dissipation	0	T _C = 25 °C	74	°C		
Maximum power dissipation	P_{D}	T _C = 100 °C	29	C		
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	W		

Revision: 16-Dec-2021 1 Document Number: 96420





Vishay Semiconductors

PARAMETER	SYMBOL	TEST CONDITIONS $I_R = 100 \ \mu A$		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}			600	-	-	
Maximum forward voltage		I _F = 15 A		-	1.3	1.7	V
	V_{FM}	I _F = 30 A	See fig. 1	-	1.5	2.0	
		I _F = 15 A, T _J = 125 °C		-	1.2	1.6	
Maximum reverse		V _R = V _R rated	Con fire O	-	1.0	10	
leakage current	I _{RM}	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See fig. 2	-	400	1000	μΑ
Junction capacitance	C _T	V _R = 200 V	See fig. 3	-	25	50	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body		-	8.0	-	nΗ

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	A/μs, V _R = 30 V	-	19	-	
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C		-	42	60	ns
oce lig. 5, 10	t _{rr2}	T _J = 125 °C	$I_F = 15 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	70	90	
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.0	6.0	- A
See fig. 6	I _{RRM2}	T _J = 125 °C		-	6.5	10	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	80	180	
See fig. 7	Q _{rr2}	T _J = 125 °C		-	220	450	IIC
Peak rate of fall of recovery current during t _b See fig. 8	dI _{(rec)M} /dt1	T _J = 25 °C		-	188	-	
	dI _{(rec)M} /dt2	T _J = 125 °C		-	160	-	A/μs

THERMAL - MECHANICAL SPECIFICATIONS PER LEG							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Junction to case, single leg conducting	D		-	-	1.7		
Junction to case, both legs conducting	- R _{thJC}		-	-	0.85	K/W	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80		
Weight			-	2.0	-	g	
Weight			-	0.07	1	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style D ² PAK (TO-263AB)	HFA30TA60CS				

Revision: 16-Dec-2021 2 Document Number: 96420

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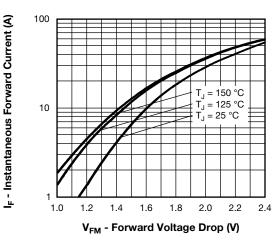


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

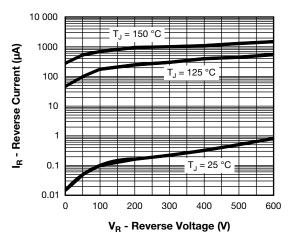


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

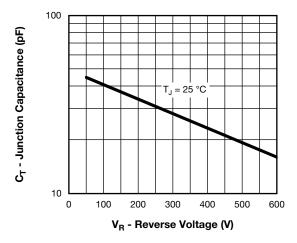


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

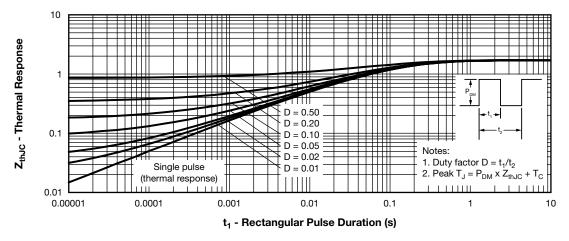


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics (Per Leg)

Revision: 16-Dec-2021 3 Document Number: 96420



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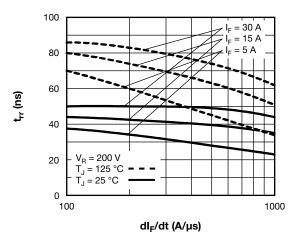


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

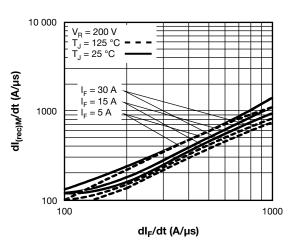


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt (Per Leg)

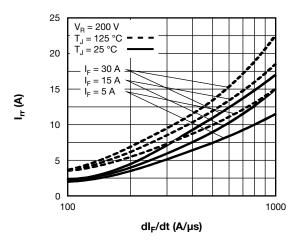


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

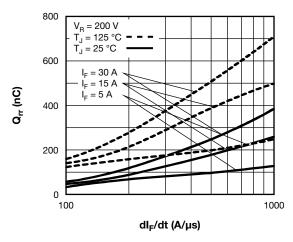
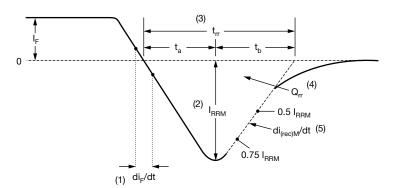


Fig. 7 - Typical Stored Charge vs. dI_F/dt (Per Leg)

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- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RBM}$

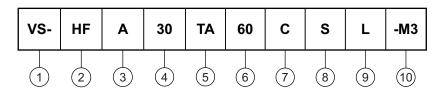
$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



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2 - HEXFRED® family

Process designator: A = electron irradiated

- Current rating (30 = 30 A)

5 - Package outline (TA = TO-220, 3 leads)

6 - Voltage rating (60 = 600 V)

Circuit configuration (C = common cathode)

8 - $S = D^2PAK (TO-263AB)$

9 - • None = tube

• L = tape and reel (left oriented)

• R = tape and reel (right oriented)

10 - Environmental digit

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free



VS-HFA30TA60CS-M3

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ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-HFA30TA60CS-M3	50	Antistatic plastic tube				
VS-HFA30TA60CSR-M3	800	13" diameter reel				
VS-HFA30TA60CSL-M3	800	13" diameter reel				

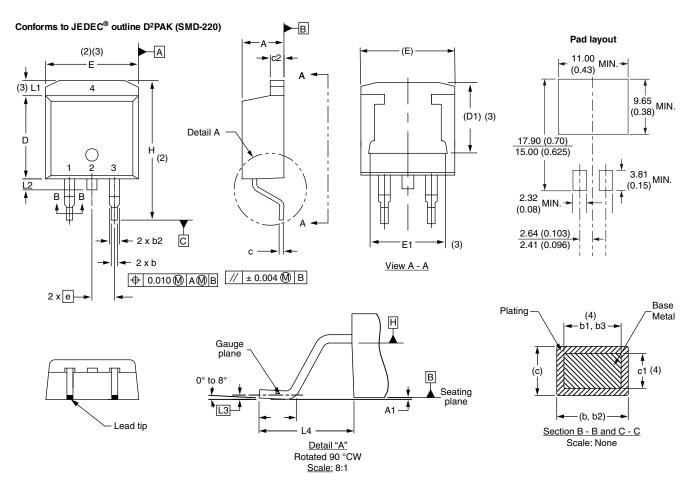
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96164			
Part marking information	www.vishay.com/doc?95444			
Packaging information	www.vishay.com/doc?96424			



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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOIES
Α	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIM	MILLIMETERS INCHES		HES	NOTES	
STINIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
D1	6.86	8.00	0.270	0.315	3	
Е	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100 BSC			
Н	14.61	15.88	0.575	0.625		
L	1.78	2.79	0.070	0.110		
L1	-	1.65	-	0.066	3	
L2	1.27	1.78	0.050	0.070		
L3	0.25	0.25 BSC		BSC		
L4	4.78	5.28	0.188	0.208		

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

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